

What is claimed is:

1. A method of planarizing a substrate having one or more materials formed thereon, comprising:  
    positioning the substrate in proximity with a polishing pad;  
    dispensing a polishing fluid to the polishing pad, the polishing fluid being subjected to carbonation prior to being dispensed to the polishing pad; and  
    polishing the substrate.
2. The method of claim 1, wherein the polishing pad is a fixed abrasive polishing pad.
3. The method of claim 2, wherein the fixed abrasive polishing pad comprises a web.
4. The method of claim 1, wherein the polishing fluid comprises a pH adjusting agent.
5. The method of claim 4, wherein the pH adjusting agent is potassium hydroxide.
6. The method of claim 1, wherein the polishing fluid comprises a buffer compound.
7. The method of claim 1, wherein the polishing fluid has a pH of from about 7 to about 12.
8. The method of claim 1, wherein the polishing fluid has a pH of from about 9.5 to about 11.5.

9. The method of claim 1, wherein the polishing fluid is carbonated for a time from about 5 to about 1000 seconds.
10. The method of claim 1, wherein the polishing fluid is carbonated for a time from about 100 to about 650 seconds.
11. The method of claim 1, wherein the substrate has a first dielectric material and a second dielectric material formed thereon.
12. The method of claim 11, wherein the first dielectric material comprises an oxide.
13. The method of claim 12, wherein the second dielectric material comprises a nitride.
14. A method of planarizing a substrate having one or more materials formed thereon, comprising:
  - positioning the substrate in proximity with a fixed abrasive polishing pad;
  - dispensing a polishing fluid to the fixed abrasive polishing pad, the polishing fluid comprising potassium hydroxide and having a pH of from about 9.5 to about 11.5 and being subjected to carbonation for about 5 to about 1000 seconds prior to being dispensed to the fixed abrasive polishing pad; and
  - polishing the substrate.
15. The method of claim 14, wherein the polishing fluid is subjected to carbonation for a time from about 100 to about 650 seconds.
16. A polishing fluid for a fixed abrasive polishing pad configured to remove materials formed on a substrate surface, comprising:
  - potassium hydroxide;
  - deionized water; and

carbon dioxide.

17. The polishing fluid of claim 16, wherein the polishing fluid has a pH of from about 7 to about 12.

18. A polishing system for planarizing one or more materials formed on a substrate surface, comprising:

a polishing platen having a polishing pad disposed thereon and in proximity to the substrate;

a controller configured to cause the polishing pad to contact the substrate;  
and

a polishing fluid delivery system adapted to deliver a polishing fluid to the polishing pad, the polishing fluid delivery system including a carbonation system.

19. The polishing system of claim 18, wherein the carbonation system is a bubbling apparatus.

20. The polishing system of claim 19, wherein the bubbling apparatus is operably connected to a gas regulator configured to control a gas flowrate into the polishing fluid.